

NGP8203N

Ignition IGBT

20 A, 400 V, N-Channel TO-220

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Overvoltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

Features

- Ideal for Coil-on-Plug and Driver-on-Coil Applications
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage for Interfacing Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- Optional Gate Resistor (R_G) and Gate-Emitter Resistor (R_{GE})

Applications

- Ignition Systems

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	440	V
Collector-Gate Voltage	V_{CER}	440	V
Gate-Emitter Voltage	V_{GE}	± 15	V
Collector Current-Continuous @ $T_C = 25^\circ\text{C}$ - Pulsed	I_C	20 50	A_{DC} A_{AC}
Continuous Gate Current	I_G	1.0	mA
Transient Gate Current ($t \leq 2$ ms, $f \leq 100$ Hz)	I_G	20	mA
ESD (Charged-Device Model)	ESD	2.0	kV
ESD (Human Body Model) $R = 1500 \Omega$, $C = 100$ pF	ESD	8.0	kV
ESD (Machine Model) $R = 0 \Omega$, $C = 200$ pF	ESD	500	V
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	150 1.0	Watts W/ $^\circ\text{C}$
Operating & Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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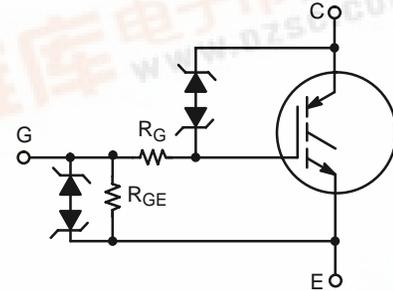
<http://onsemi.com>

20 AMPS

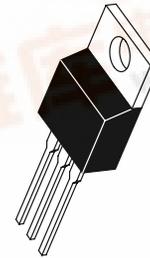
400 VOLTS

$V_{CE(on)} = 1.3 \text{ V @}$

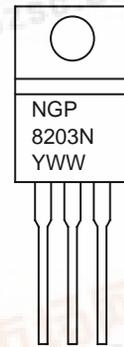
$I_C = 10 \text{ A}, V_{GE} \geq 4.5 \text{ V}$



MARKING DIAGRAM



TO-220
CASE 221A
STYLE 9



NGP8203N = Device Code
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NGP8203N	TO-220	50 Units / Rail



NGP8203N

UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS ($-55^{\circ} \leq T_J \leq 175^{\circ}\text{C}$)

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy $V_{CC} = 50\text{ V}$, $V_{GE} = 5.0\text{ V}$, $\text{Pk } I_L = 16.7\text{ A}$, $R_G = 1000\ \Omega$, $L = 1.8\text{ mH}$, Starting $T_J = 25^{\circ}\text{C}$ $V_{CC} = 50\text{ V}$, $V_{GE} = 5.0\text{ V}$, $\text{Pk } I_L = 14.9\text{ A}$, $R_G = 1000\ \Omega$, $L = 1.8\text{ mH}$, Starting $T_J = 150^{\circ}\text{C}$ $V_{CC} = 50\text{ V}$, $V_{GE} = 5.0\text{ V}$, $\text{Pk } I_L = 14.1\text{ A}$, $R_G = 1000\ \Omega$, $L = 1.8\text{ mH}$, Starting $T_J = 175^{\circ}\text{C}$	E_{AS}	250 200 180	mJ
Reverse Avalanche Energy $V_{CC} = 100\text{ V}$, $V_{GE} = 20\text{ V}$, $\text{Pk } I_L = 25.8\text{ A}$, $L = 6.0\text{ mH}$, Starting $T_J = 25^{\circ}\text{C}$	$E_{AS(R)}$	2000	mJ

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^{\circ}\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$
Maximum Temperature for Soldering Purposes, 1/8" from case for 5 seconds (Note 1)	T_L	275	$^{\circ}\text{C}$

1. For further details, see Soldering and Mounting Techniques Reference Manual: SOLDERRM/D.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Clamp Voltage	BV_{CES}	$I_C = 2.0\text{ mA}$	$T_J = -40^{\circ}\text{C to } 175^{\circ}\text{C}$	370	395	420	V
		$I_C = 10\text{ mA}$	$T_J = -40^{\circ}\text{C to } 175^{\circ}\text{C}$	390	415	440	
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 15\text{ V}$	$T_J = 25^{\circ}\text{C}$		0.1	1.0	μA
			$T_J = 175^{\circ}\text{C}$	0.5	1.5	10	
		$V_{CE} = 200\text{ V}$, $V_{GE} = 0\text{ V}$	$T_J = 175^{\circ}\text{C}$	1.0	25	100*	μA
			$T_J = -40^{\circ}\text{C}$	0.4	0.8	5.0	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75\text{ mA}$	$T_J = 25^{\circ}\text{C}$	30	35	39	V
			$T_J = 175^{\circ}\text{C}$	35	39	45*	
			$T_J = -40^{\circ}\text{C}$	30	33	37	
Reverse Collector-Emitter Leakage Current	$I_{CES(R)}$	$V_{CE} = -24\text{ V}$	$T_J = 25^{\circ}\text{C}$	0.05	0.1	0.5	mA
			$T_J = 175^{\circ}\text{C}$	1.0	5.0	10*	
			$T_J = -40^{\circ}\text{C}$	0.005	0.01	0.1	
Gate-Emitter Clamp Voltage	BV_{GES}	$I_G = \pm 5.0\text{ mA}$	$T_J = -40^{\circ}\text{C to } 175^{\circ}\text{C}$	12	12.5	14	V
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 5.0\text{ V}$	$T_J = -40^{\circ}\text{C to } 175^{\circ}\text{C}$	200	300	350*	μA
Gate Resistor (Optional)	R_G		$T_J = -40^{\circ}\text{C to } 175^{\circ}\text{C}$		70		Ω
Gate-Emitter Resistor	R_{GE}		$T_J = -40^{\circ}\text{C to } 175^{\circ}\text{C}$	14.25	16	25	k Ω

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0\text{ mA}$, $V_{GE} = V_{CE}$	$T_J = 25^{\circ}\text{C}$	1.5	1.8	2.1	V
			$T_J = 175^{\circ}\text{C}$	0.7	1.0	1.3	
			$T_J = -40^{\circ}\text{C}$	1.7	2.0	2.3*	
Threshold Temperature Coefficient (Negative)				4.0	4.6	5.2	mV/ $^{\circ}\text{C}$

*Maximum Value of Characteristic across Temperature Range.

2. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

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ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 3)							
Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 6.5 \text{ A}$, $V_{GE} = 3.7 \text{ V}$	$T_J = 25^\circ\text{C}$	0.95	1.15	1.35	V
			$T_J = 175^\circ\text{C}$	0.7	0.95	1.15	
			$T_J = -40^\circ\text{C}$	1.0	1.3	1.40	
		$I_C = 9.0 \text{ A}$, $V_{GE} = 3.9 \text{ V}$	$T_J = 25^\circ\text{C}$	0.95	1.25	1.45	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.25	
			$T_J = -40^\circ\text{C}$	1.1	1.4	1.5	
		$I_C = 7.5 \text{ A}$, $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	0.85	1.15	1.4	
			$T_J = 175^\circ\text{C}$	0.7	0.95	1.2	
			$T_J = -40^\circ\text{C}$	1.0	1.3	1.6*	
		$I_C = 10 \text{ A}$, $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.3	1.6	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.4	
			$T_J = -40^\circ\text{C}$	1.1	1.4	1.7*	
		$I_C = 15 \text{ A}$, $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.15	1.45	1.7	
			$T_J = 175^\circ\text{C}$	1.0	1.3	1.55	
			$T_J = -40^\circ\text{C}$	1.25	1.55	1.8*	
		$I_C = 20 \text{ A}$, $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.3	1.6	1.9	
			$T_J = 175^\circ\text{C}$	1.2	1.5	1.8	
			$T_J = -40^\circ\text{C}$	1.4	1.75	2.0*	
Forward Transconductance	gfs	$I_C = 6.0 \text{ A}$, $V_{CE} = 5.0 \text{ V}$	$T_J = 25^\circ\text{C}$	10	18	25	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{ISS}	$f = 10 \text{ kHz}$, $V_{CE} = 25 \text{ V}$	$T_J = 25^\circ\text{C}$	1100	1300	1500	pF
Output Capacitance	C_{OSS}			70	80	90	
Transfer Capacitance	C_{RSS}			18	20	22	

SWITCHING CHARACTERISTICS

Turn-Off Delay Time (Resistive)	$t_{d(off)}$	$V_{CC} = 300 \text{ V}$, $I_C = 9.0 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$, $R_L = 33 \Omega$, $V_{GE} = 5.0 \text{ V}$	$T_J = 25^\circ\text{C}$	6.0	8.0	10	μSec
Fall Time (Resistive)	t_f		$T_J = 175^\circ\text{C}$	6.0	8.0	10	
			$T_J = 25^\circ\text{C}$	4.0	6.0	8.0	
			$T_J = 175^\circ\text{C}$	8.0	10.5	14	
Turn-Off Delay Time (Inductive)	$t_{d(off)}$	$V_{CC} = 300 \text{ V}$, $I_C = 9.0 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$, $L = 300 \mu\text{H}$, $V_{GE} = 5.0 \text{ V}$	$T_J = 25^\circ\text{C}$	3.0	5.0	7.0	μSec
Fall Time (Inductive)	t_f		$T_J = 175^\circ\text{C}$	5.0	7.0	9.0	
			$T_J = 25^\circ\text{C}$	1.5	3.0	4.5	
			$T_J = 175^\circ\text{C}$	5.0	7.0	10	
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 14 \text{ V}$, $I_C = 9.0 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$, $R_L = 1.5 \Omega$, $V_{GE} = 5.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.5	2.0	μSec
Rise Time	t_r		$T_J = 175^\circ\text{C}$	1.0	1.5	2.0	
			$T_J = 25^\circ\text{C}$	4.0	6.0	8.0	
			$T_J = 175^\circ\text{C}$	3.0	5.0	7.0	

*Maximum Value of Characteristic across Temperature Range.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

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TYPICAL ELECTRICAL CHARACTERISTICS

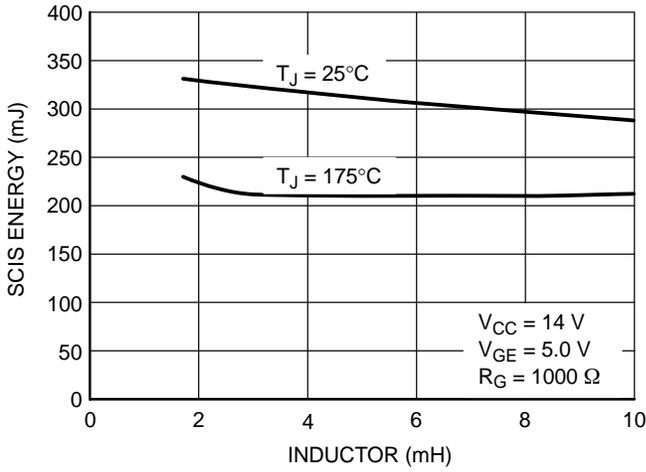


Figure 1. Self Clamped Inductive Switching

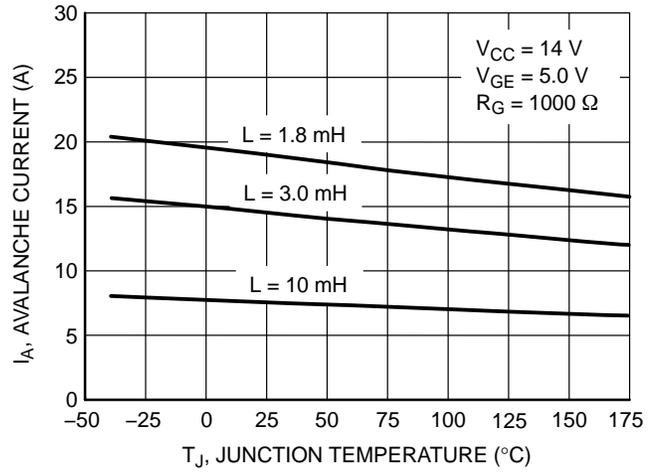


Figure 2. Open Secondary Avalanche Current vs. Temperature

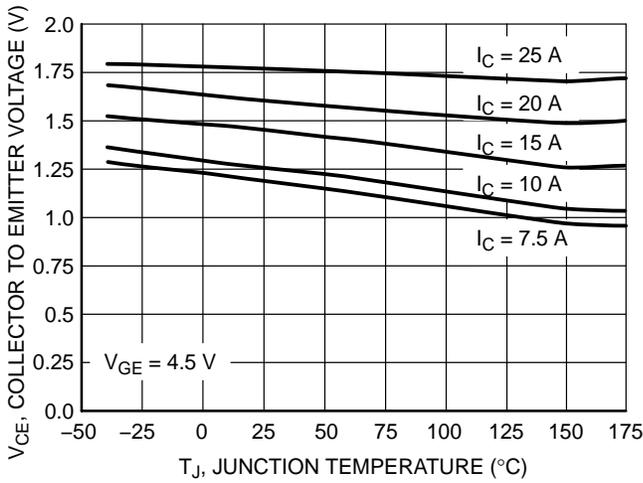


Figure 3. Collector-to-Emitter Voltage vs. Junction Temperature

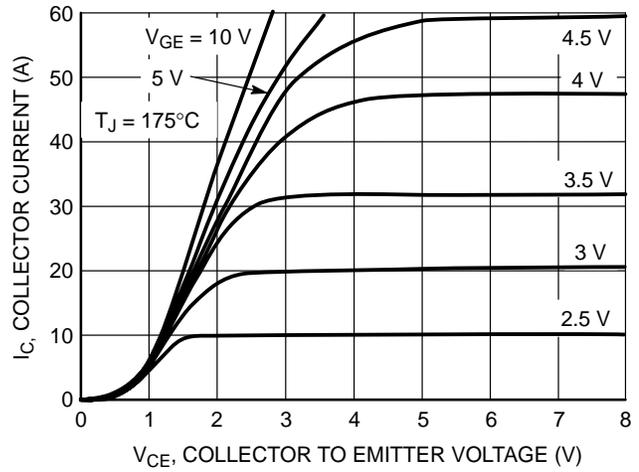


Figure 4. Collector Current vs. Collector-to-Emitter Voltage

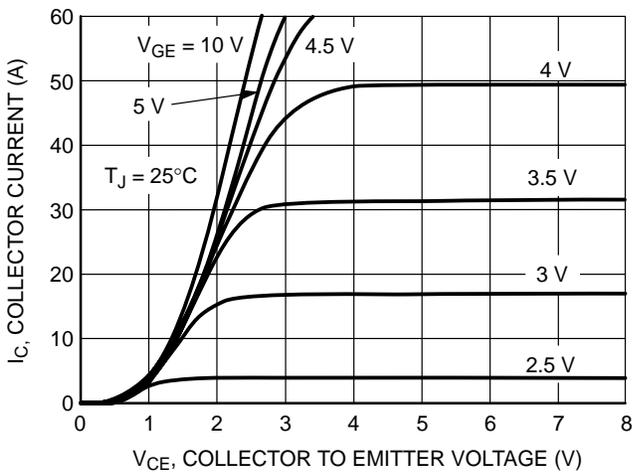


Figure 5. Collector Current vs. Collector-to-Emitter Voltage

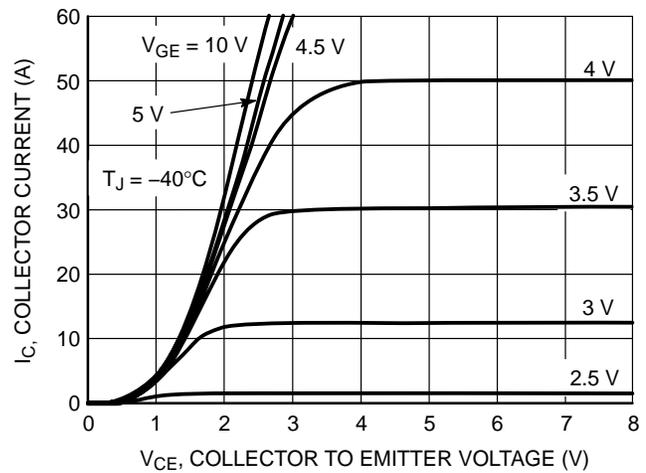


Figure 6. Collector Current vs. Collector-to-Emitter Voltage

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TYPICAL ELECTRICAL CHARACTERISTICS

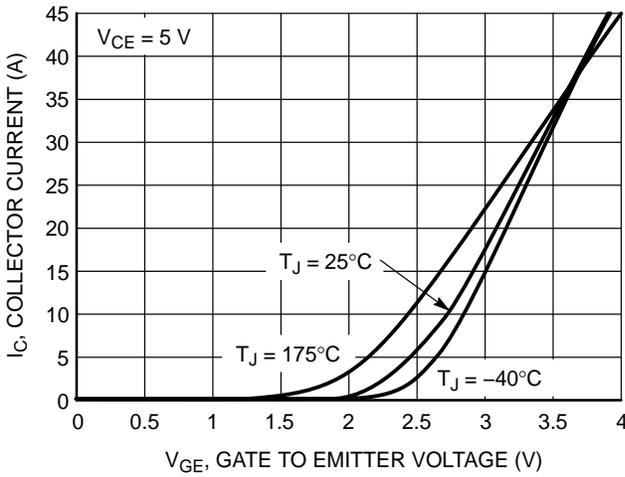


Figure 7. Transfer Characteristics

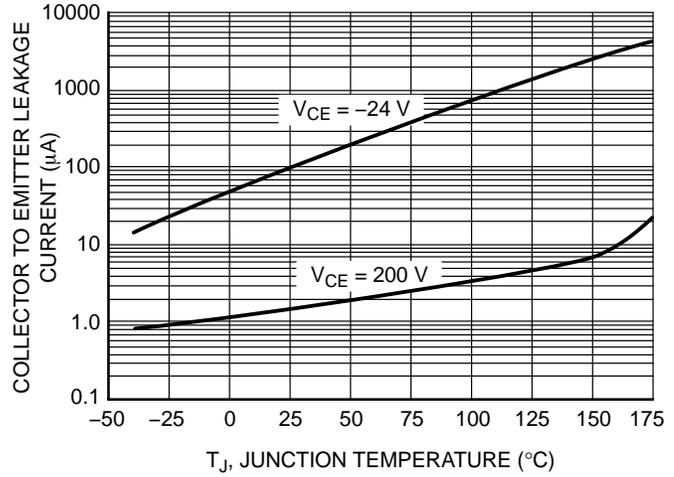


Figure 8. Collector-to-Emitter Leakage Current vs. Temperature

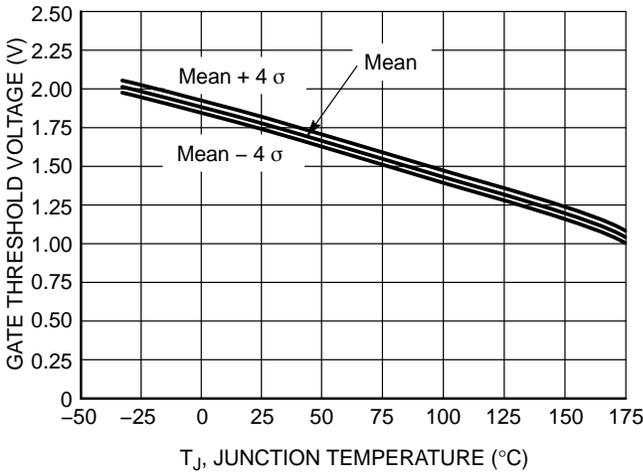


Figure 9. Gate Threshold Voltage vs. Temperature

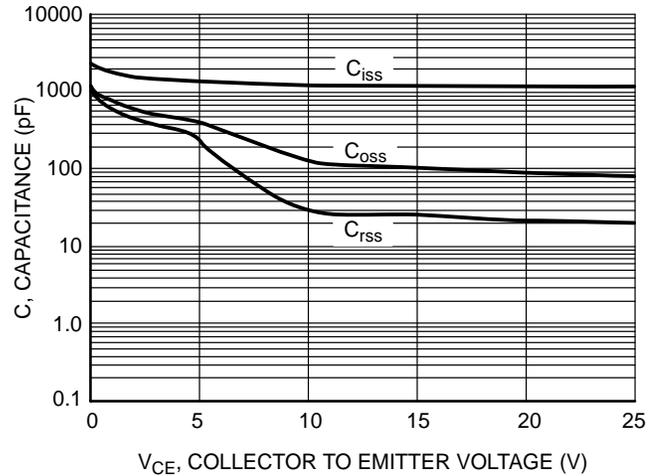


Figure 10. Capacitance vs. Collector-to-Emitter Voltage

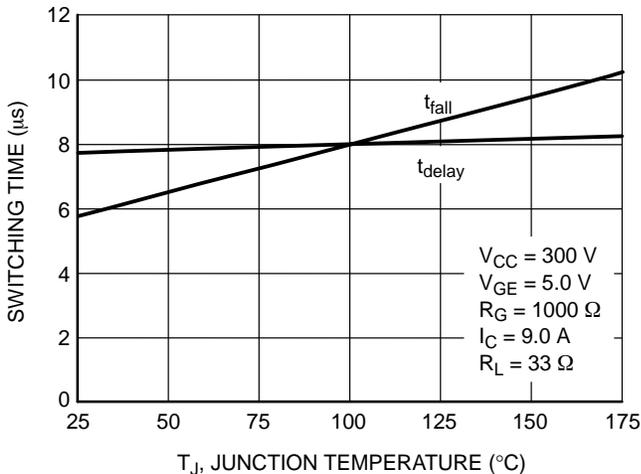


Figure 11. Resistive Switching Fall Time vs. Temperature

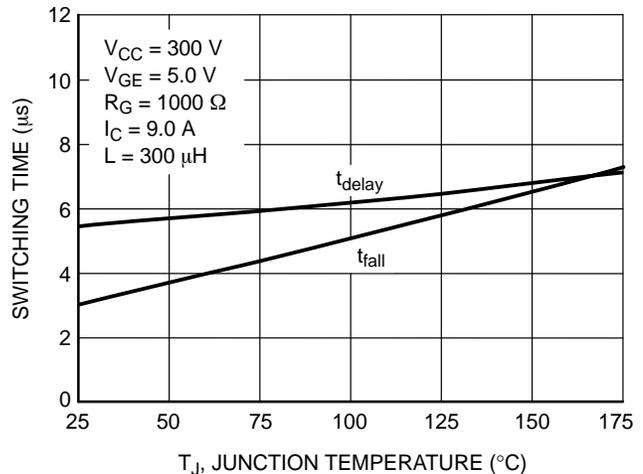


Figure 12. Inductive Switching Fall Time vs. Temperature

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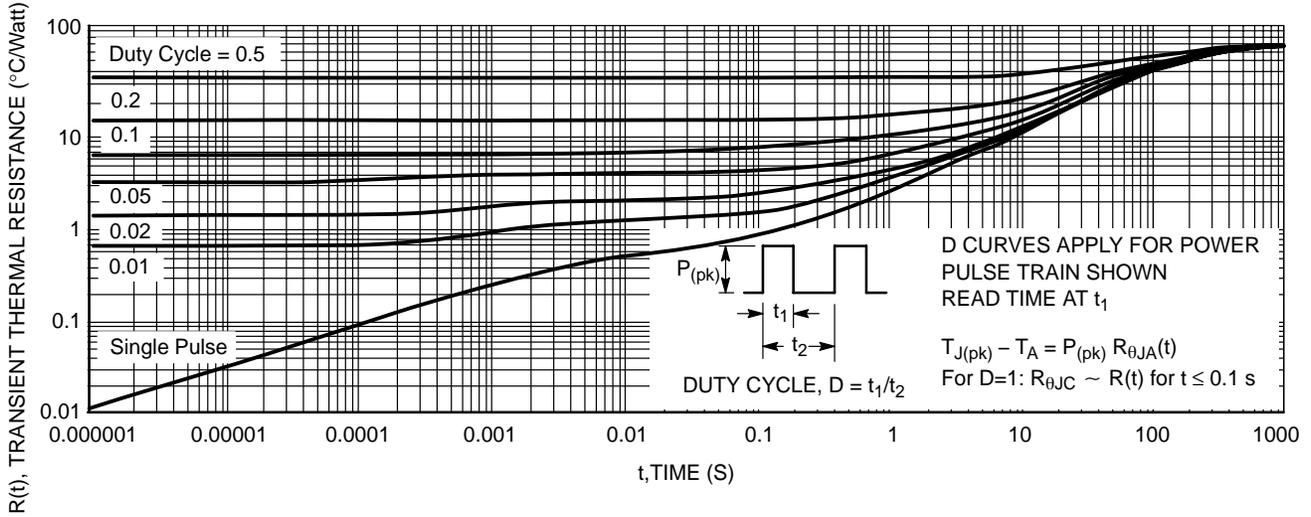


Figure 13. Transient Thermal Resistance (Non-normalized Junction-to-Ambient)

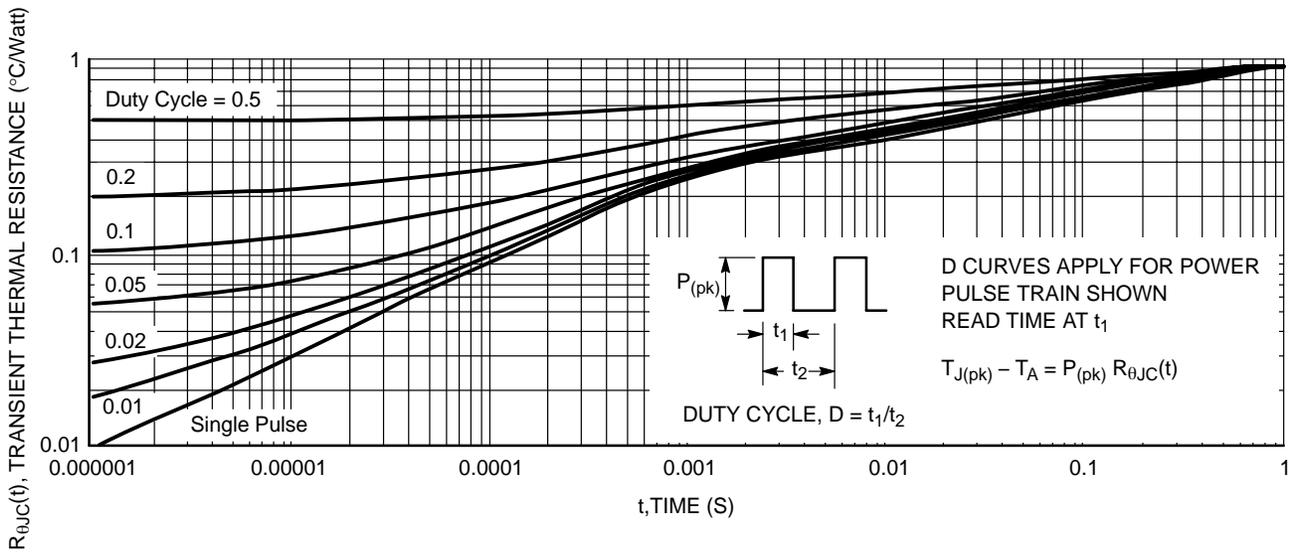
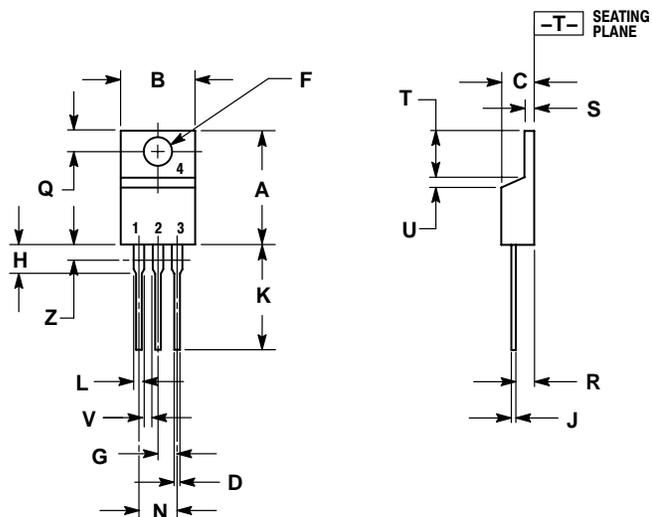


Figure 14. Best Case Transient Thermal Resistance (Non-normalized Junction-to-Case Mounted on Cold Plate)

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PACKAGE DIMENSIONS

TO-220
CASE 221A-07
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

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